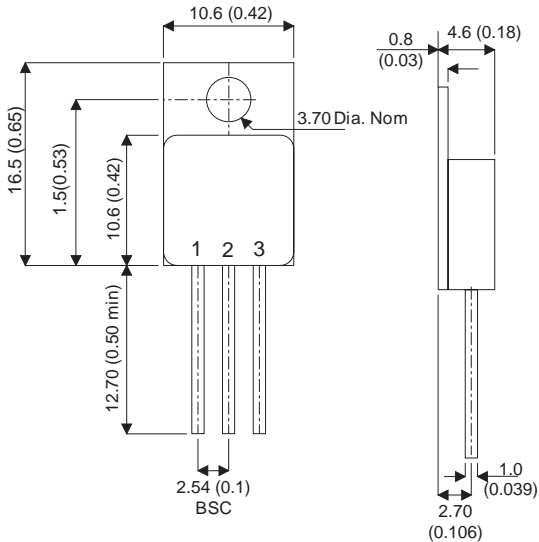


MECHANICAL DATA

Dimensions in mm



TO220 (TO-257AB) METAL PACKAGE

**DUAL SCHOTTKY
 BARRIER DIODE IN
 TO220 METAL PACKAGE
 FOR HI-REL APPLICATIONS**

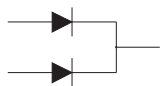
FEATURES

- HERMETIC TO220 METAL PACKAGE
- SCREENING OPTIONS AVAILABLE
- OUTPUT CURRENT 16A(8A per leg)
- LOW V_F
- LOW LEAKAGE
- ISOLATED CASE

ELECTRICAL CONNECTIONS

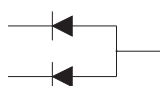
Common Cathode Common Anode Series Connection

SB08-100M



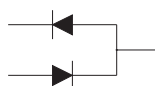
1 = A₁ Anode 1
 2 = K Cathode
 3 = A₂ Anode 2

SB08-100AM



1 = K₁ Cathode 1
 2 = A Anode
 3 = K₂ Cathode 2

SB08-100RM



1 = K₁ Cathode 1
 2 = Centre Tap
 3 = A₂ Anode

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

		SB08 - 100M SB08 - 100AM SB08 - 100RM
V_{RRM}	Peak Repetitive Reverse Voltage	100V
V_{RSM}	Peak Non-Repetitive Reverse Voltage	100V
V_R	Continuous Reverse Voltage	100V
I_O	Output Current	8A
I_{FSM}	Peak Non-Repetitive Surge Current (50Hz)	275A
T_{STG}	Storage Temperature Range	-55°C to 175°C
T_J	Maximum Operating Junction Temperature	175°C

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

ELECTRICAL CHARACTERISTICS (Per Diode) $T_{CASE} = 25^{\circ}C$ unless otherwise stated

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{FM} Max Forward Voltage (per diode)	$I_F = 8A^*$ $T_J = 25^{\circ}C$			0.75	V
	$I_F = 16A^*$ $T_J = 25^{\circ}C$			0.95	
	$I_F = 8A^*$ $T_J = 125^{\circ}C$			0.60	
	$I_F = 16A^*$ $T_J = 125^{\circ}C$			0.75	
I_{RM} Reverse Current (per diode)	$V_R = V_{RRM}^*$ $T_J = 125^{\circ}C$			7	mA
	$V_R = V_{RRM}$ $T_J = 25^{\circ}C$			550	μA
C_T Junction Capacitance (per diode)	$V_R = 5 V$ $f = 1 MHz$		500		pF
$I_{F(AV)}$ Max Average Forward Current	50% Duty Cycle Per Diode			8	A
	50% Duty Cycle Per Device			16	

*Pulse test $t_p=300\mu s$ $\delta \leq 2\%$

Parameter	Unit
$R_{TH(j-c)}$ Maximum Thermal Resistance Junction To Case	1.5 $^{\circ}C/W$